

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	42766	semiconductor and substrate and node electrical adj charge and signale adj bit	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/11 13:30
L2	42966	semiconductor and substrate and node electrical adj charge and single adj bit and digital	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/11 13:31
L3	1070579	capacitor wit hnode	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/11 13:31
L4	9044	capacitor with coupled with node	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/11 13:32
L5	1609	4 and first adj capacitor and transistor and second adj capacitor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/11 13:32
L6	41	5 and type with capacitive	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/11 13:36
L7	41	6 and first adj capacitor and second adj capacitor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/11 14:08
L8	1	7 and first adj type with capacitive and second adj type with capacitive adj structure	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/11 13:38

EAST Search History

L9	1	first adj type with capacitive and second adj type with capacitive adj structure	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/11 13:39
L10	50	first adj type with capacitive and second adj type with capacitive	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/11 13:39
L11	15	10 and first adj capacitor and second adj capacitor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/11 13:39
L12	1	11 and (bitline or bit adj line or bit-line)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/11 13:40
L13	7	11 and transistors and associated	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/11 13:42
L14	1105	substrate and trench adj capacitor and stacked adj capacitor and (bitline or bit adj line or bit-line)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/11 13:44
L15	1072	14 and transistors	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/11 13:44
L16	365	15 and transistors with semiconductor adj substrate	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/11 13:45

EAST Search History

L17	96	15 and transistors with semiconductor adj substrate with (bitline or bit adj line or bit-line)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/11 13:45
L18	1	17 and transistor\$1 with individually	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/11 13:46
L19	11	("20020009874" "20030042489" "3387282" "5106774" "5920785" "6184548").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/11 14:07
L20	0	265/149.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/11 14:07
L21	0	20 and first adj capacitor and second adj capacitor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/11 14:08
L22	0	20 and first adj capacitor and second adj capacitor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/11 14:08
L23	634	first with second with capacitor\$1 with capacitor adj pair	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/11 14:09
L24	269	first with second with capacitor\$1 with capacitor adj pair.clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/11 14:09

EAST Search History

L25	269	(first with second with capacitor\$1 with capacitor adj pair).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/11 14:09
L26	269	(first with second with capacitor\$1 with capacitor adj pair).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/11 14:10
L27	792	(first with second with capacitor\$1 with first adj capacitor adj pair with second capacitor adj pair).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/11 14:10
L28	18	(first with second with capacitor\$1 with first adj capacitor adj pair with second adj capacitor adj pair).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/11 14:12
L29	1	28 and transistor and first adj type and second adj type	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/11 14:12